02PN004A-US
GT71H-US

Fig.1

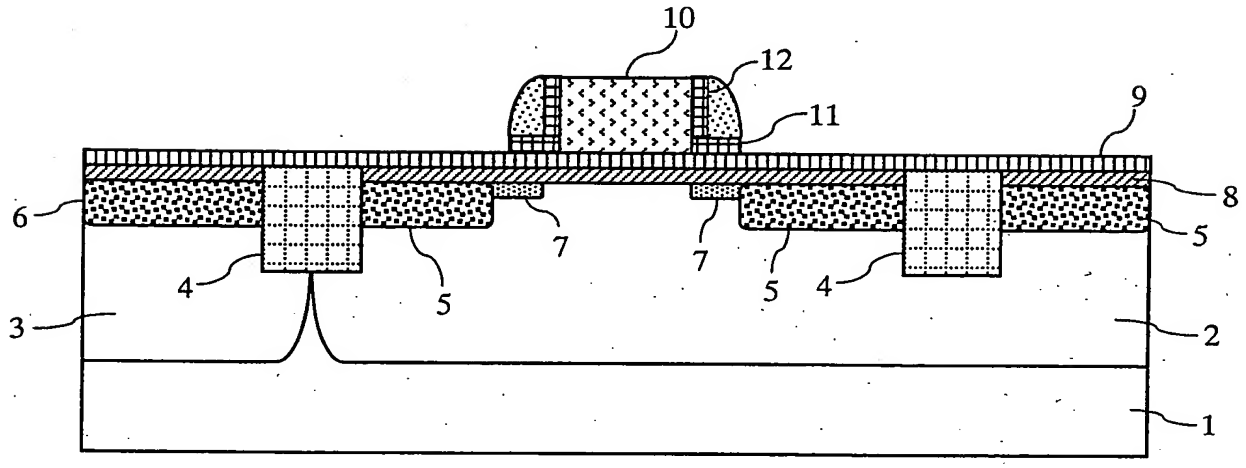


Fig.2A

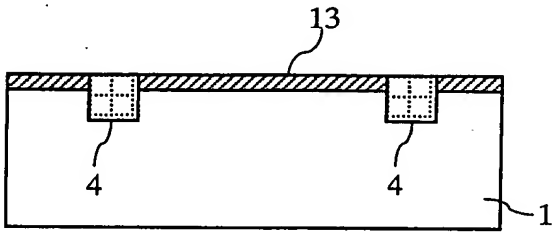


Fig.2B

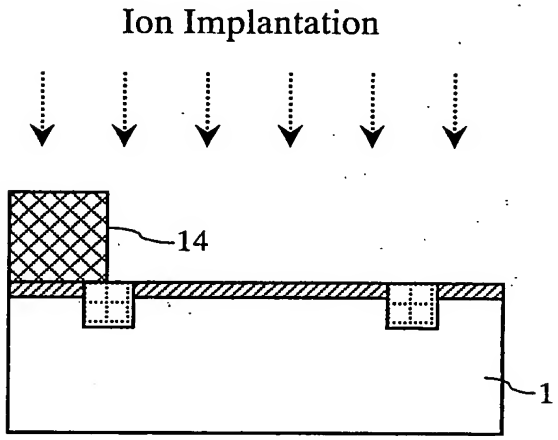


Fig.2C

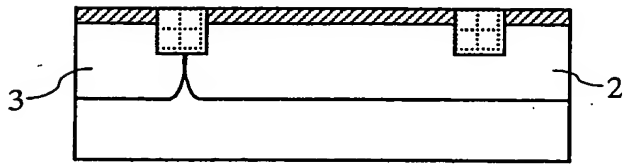


Fig.2D

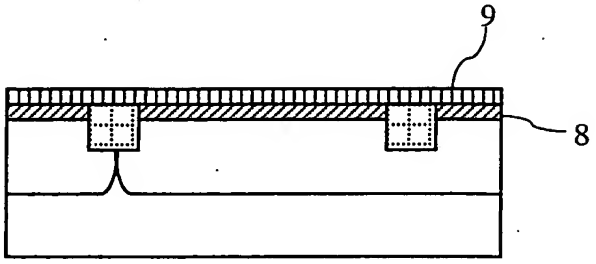


Fig.2E

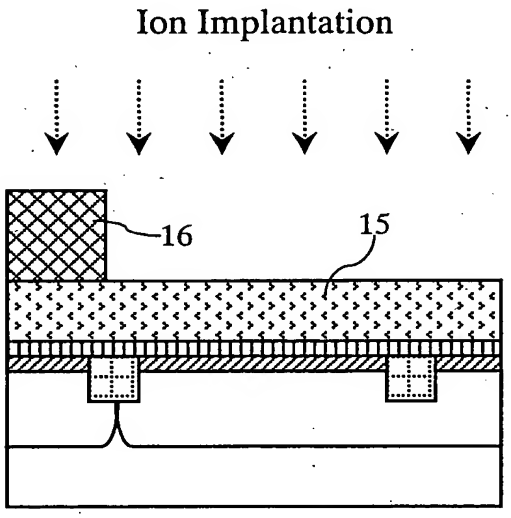


Fig.2F

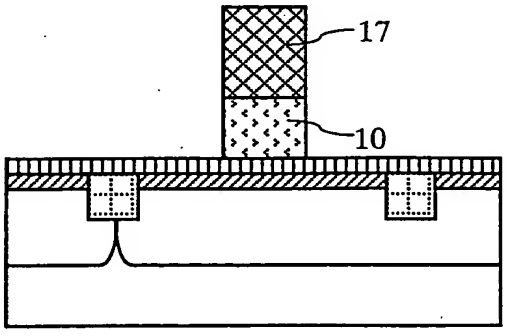


Fig.3A

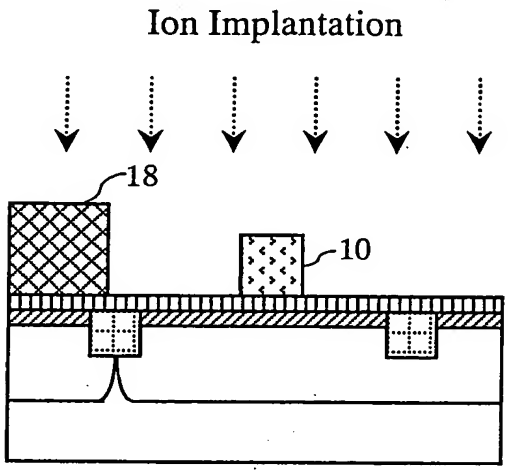


Fig.3B

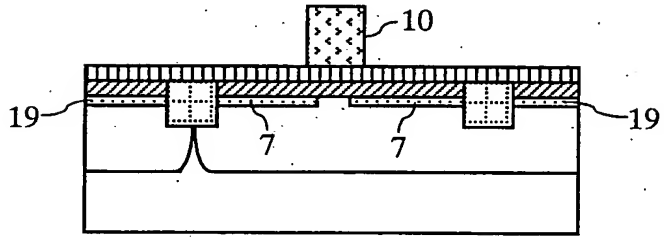


Fig.3C

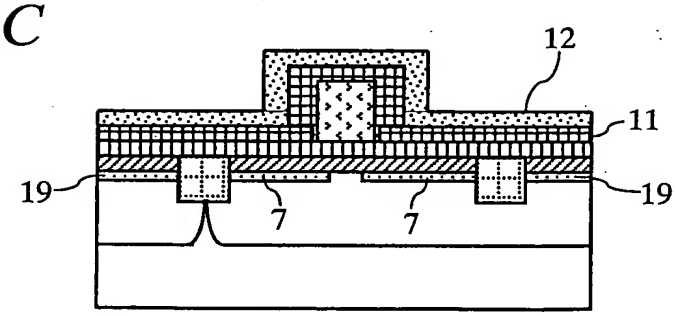


Fig.3D

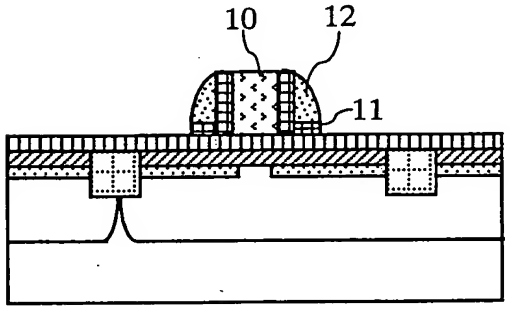


Fig.3E

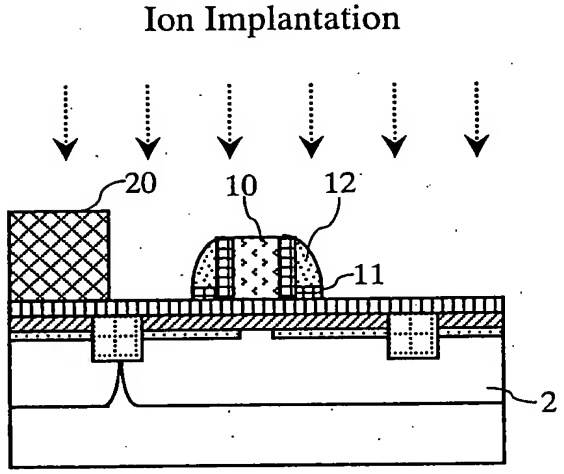


Fig.3F

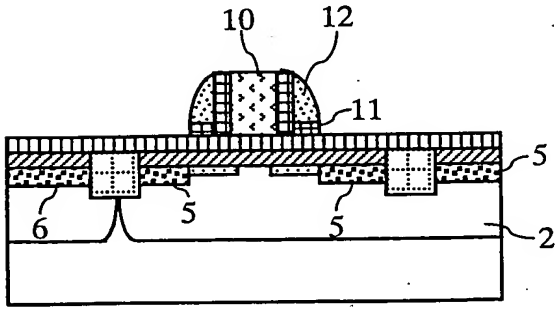


Fig.4

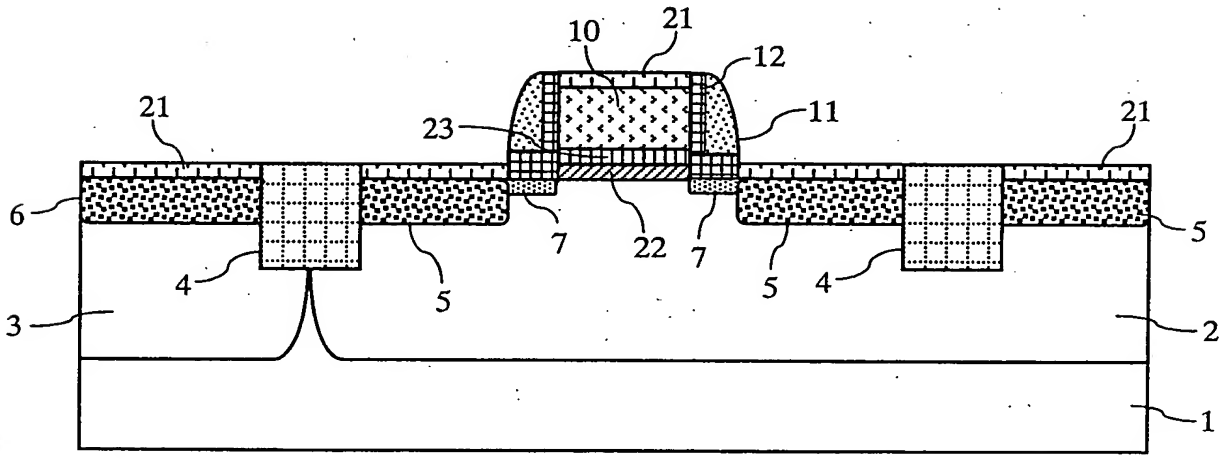
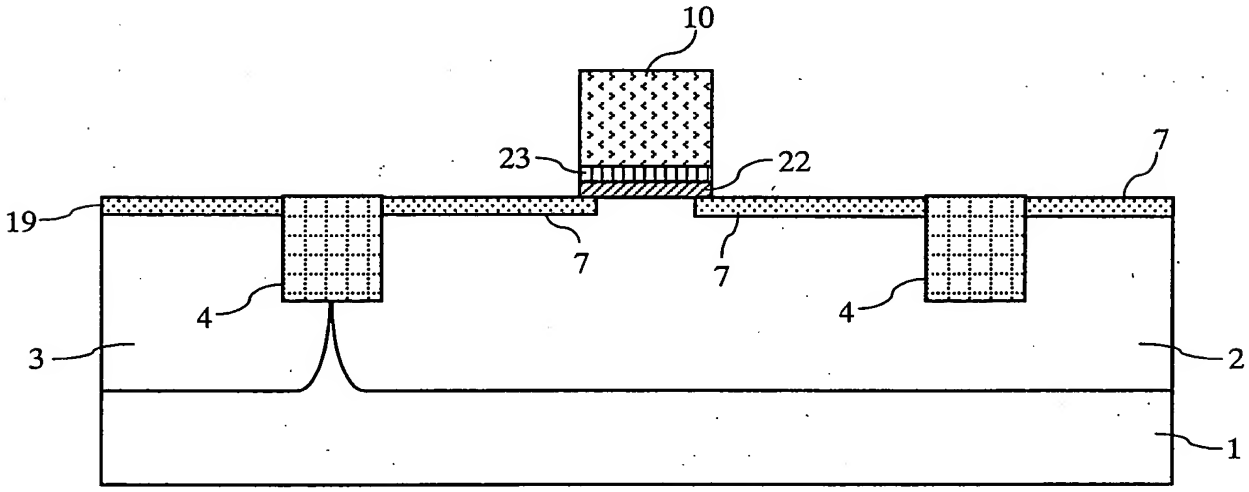


Fig.5



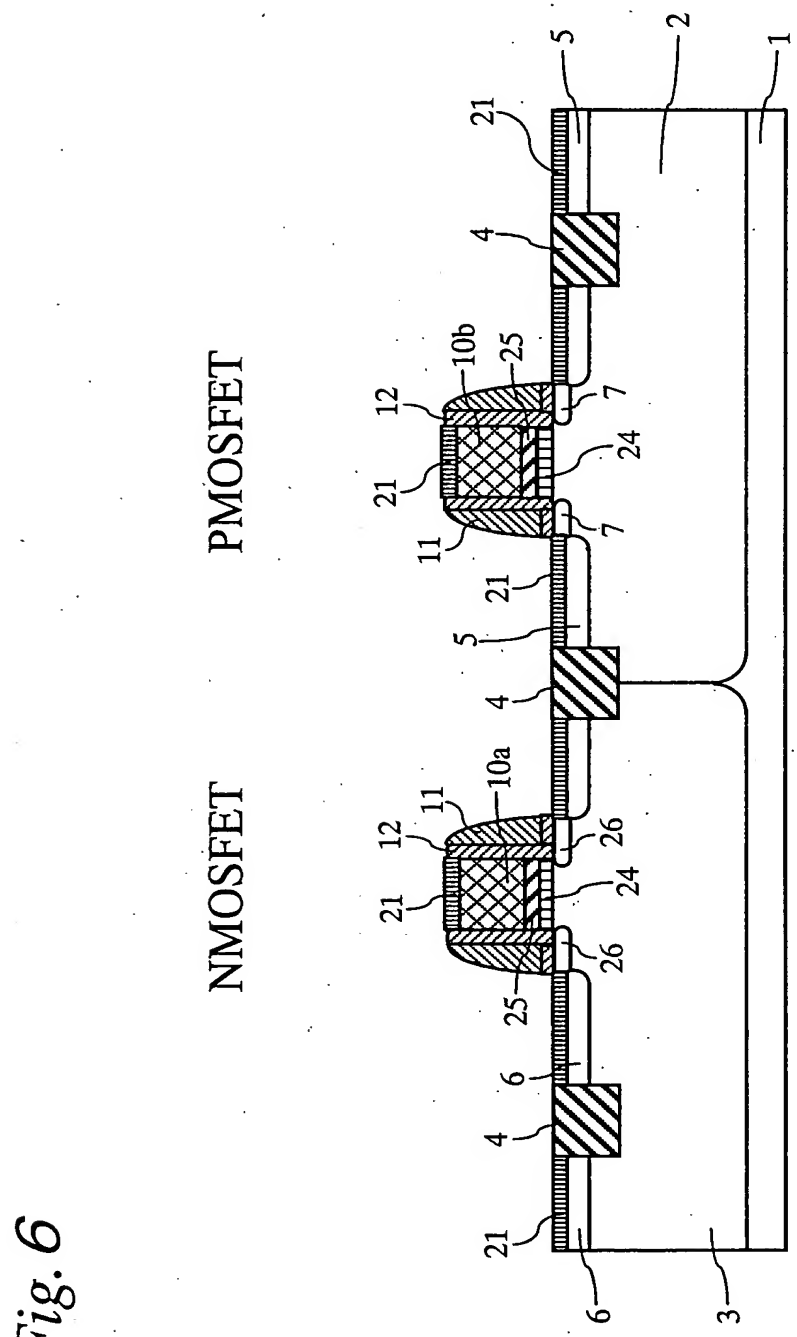
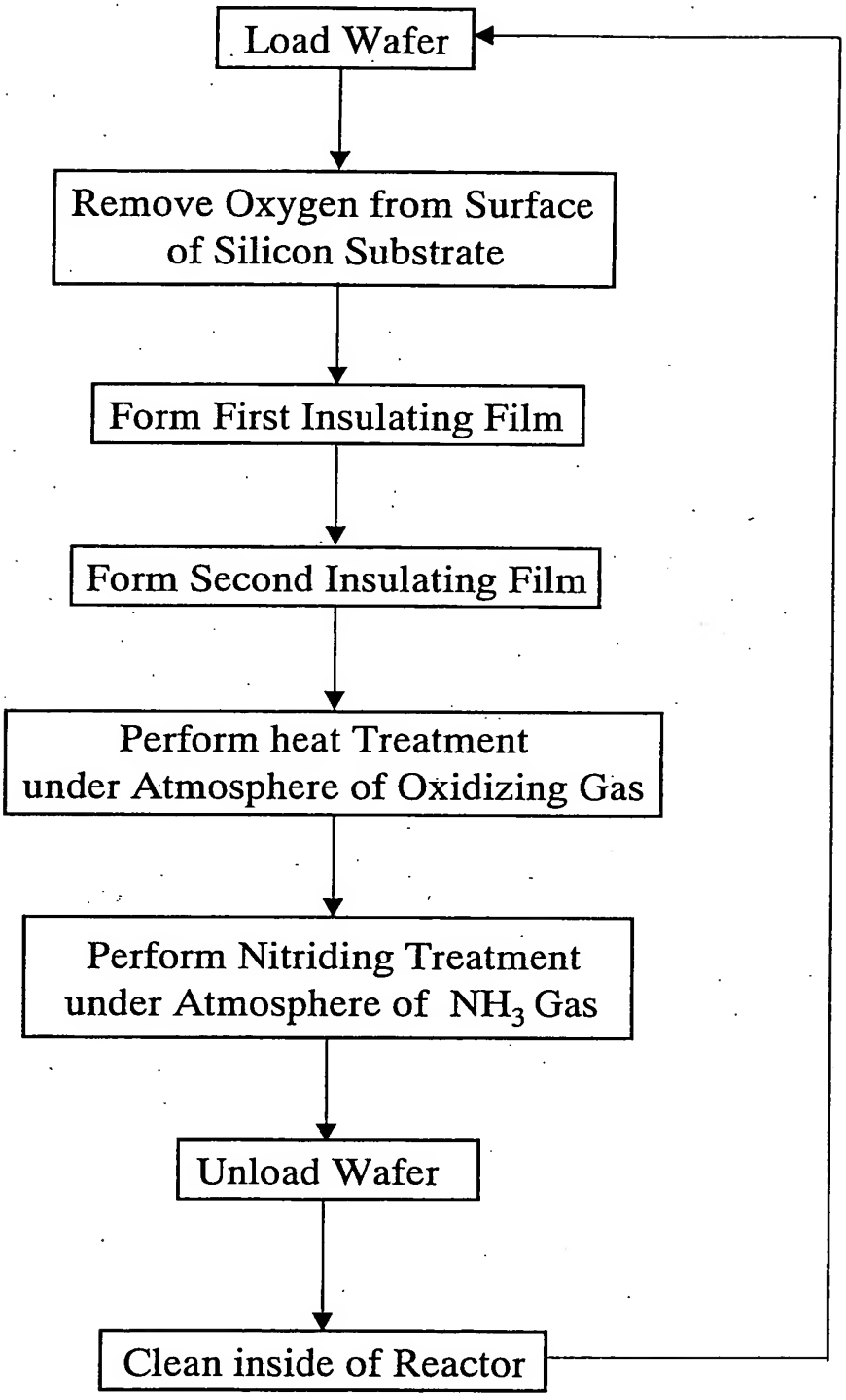


Fig. 6

Fig. 7


Load Wafer
Remove Oxygen from Surface of Silicon Substrate
Form First Insulating Film
Form Second Insulating Film
Perform heat Treatment under Atmosphere of Oxidizing Gas
Perform Nitriding Treatment under Atmosphere of NH_3 Gas
Unload Wafer
Clean inside of Reactor